

# Revolutionary Components based on High-Performance Materials



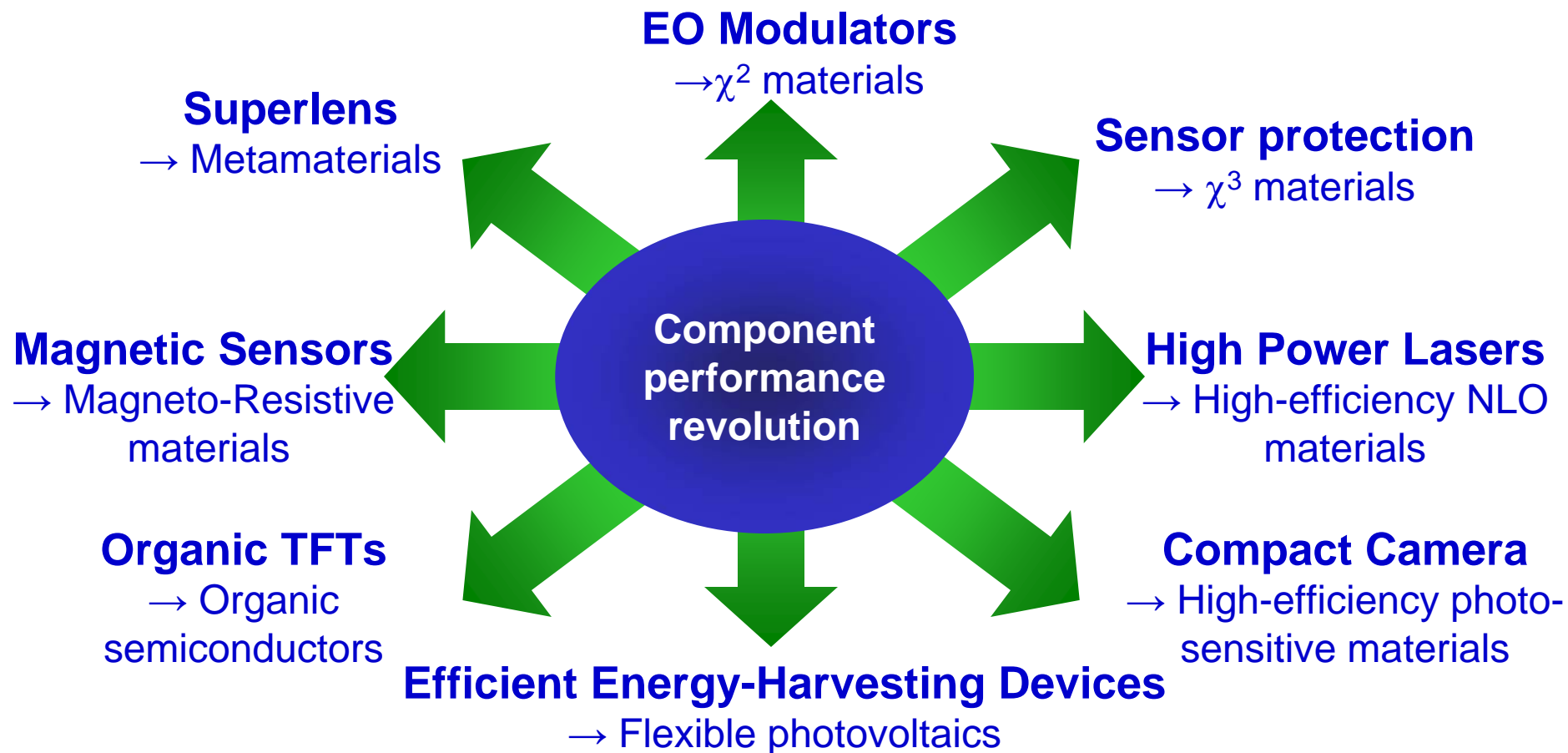
Dev Shenoy, PhD

DARPA/MTO

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# Components and Devices for the Future Military



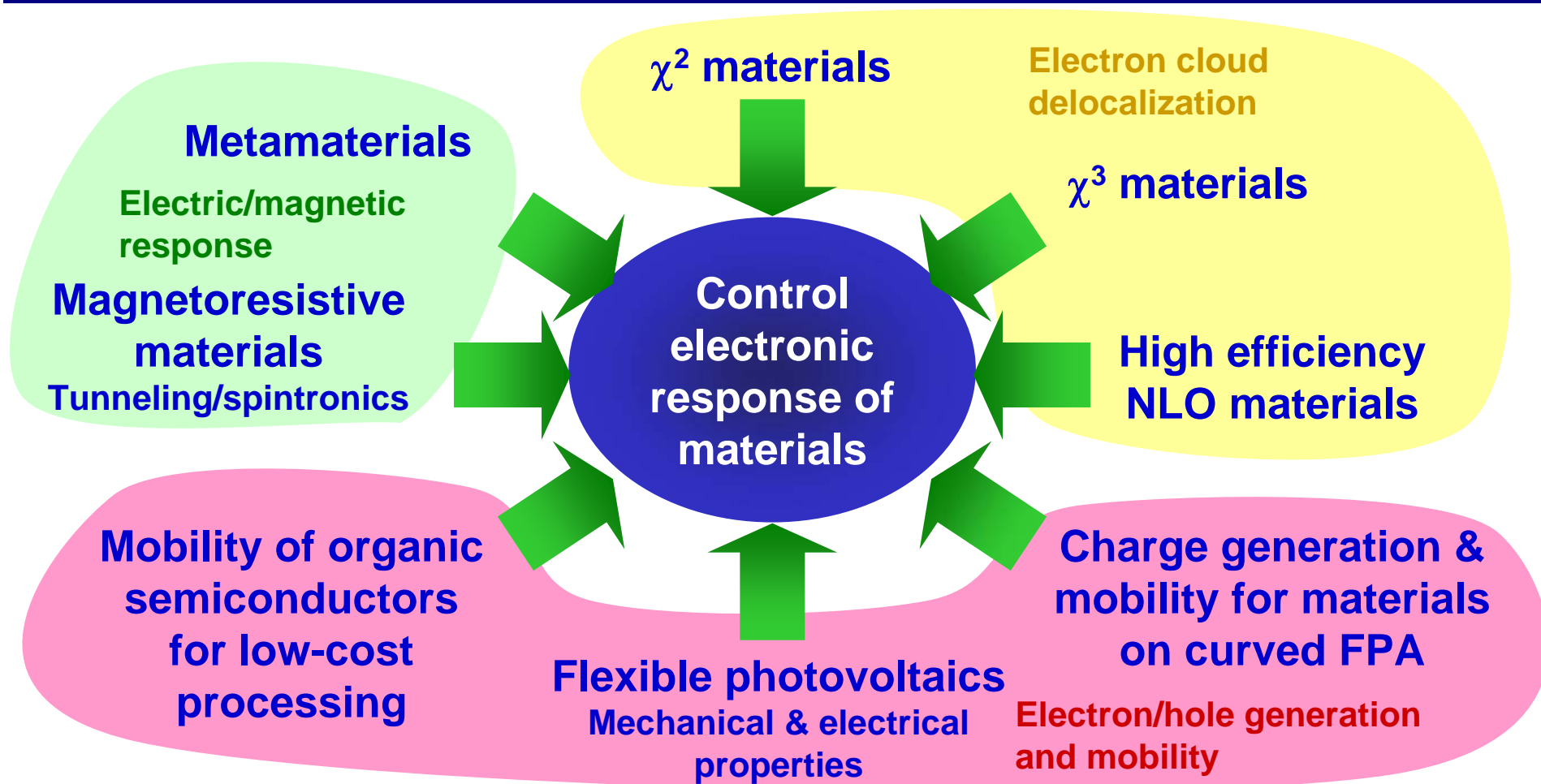
**Leverage High-Performance Materials for Revolutionary Photonic, Electronic, & Magnetic Components**

Dr. Devanand Shenoy

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# Engineering at the Nanoscale



**Control of electronic and photonic properties at the nanoscale to drive material and device performance**

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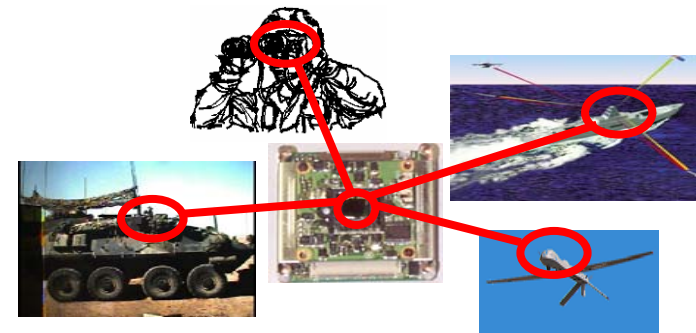


# MORPH PROGRAM

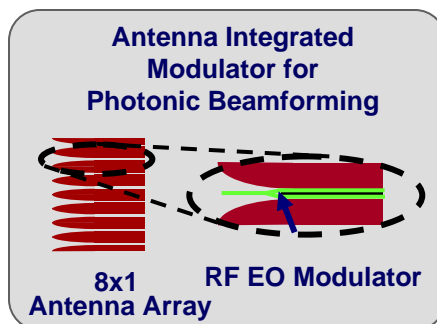
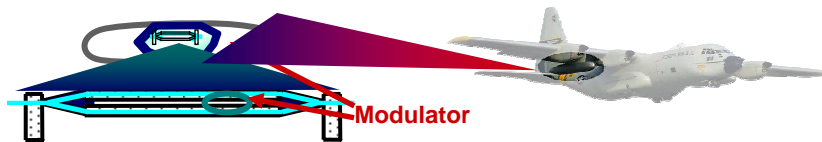


## Objectives:

- Develop highly non-linear optical materials for applications in RF photonics and sensor protection
- Develop high-bandwidth, low drive-voltage EO modulators



Protect from ultra-short pulsed and broadband tunable lasers



Flexible polymer modulator

## Military Impact:

- Enhanced Performance of Phased Array Radar
- Protection for DoD personnel and sensor systems from laser threats



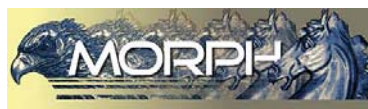


# EO Modulators

## $\chi^{(2)}$ Materials and Components

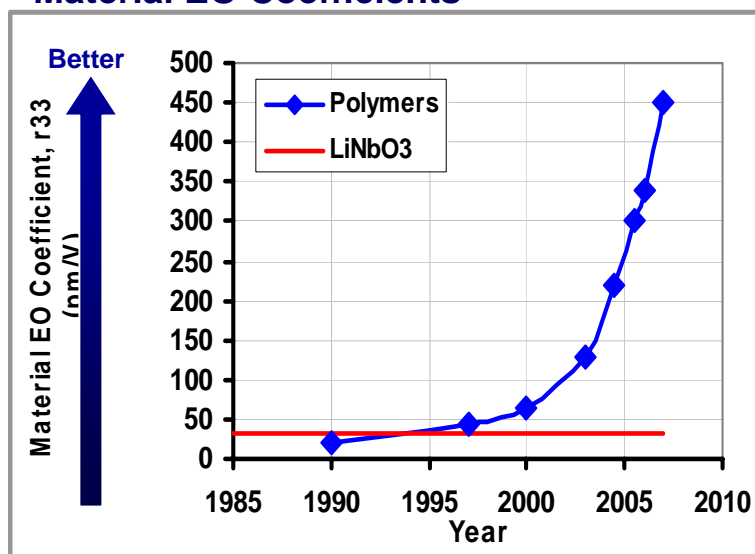


### Program Goals



NLO coefficient $r_{33}$ @1.5 $\mu\text{m}$	>1200 pm/V
Absorption loss	<1 dB/cm
Polymer $T_g$	>200 C
Fiber coupling	<0.75 dB
Bandwidth	100 GHz

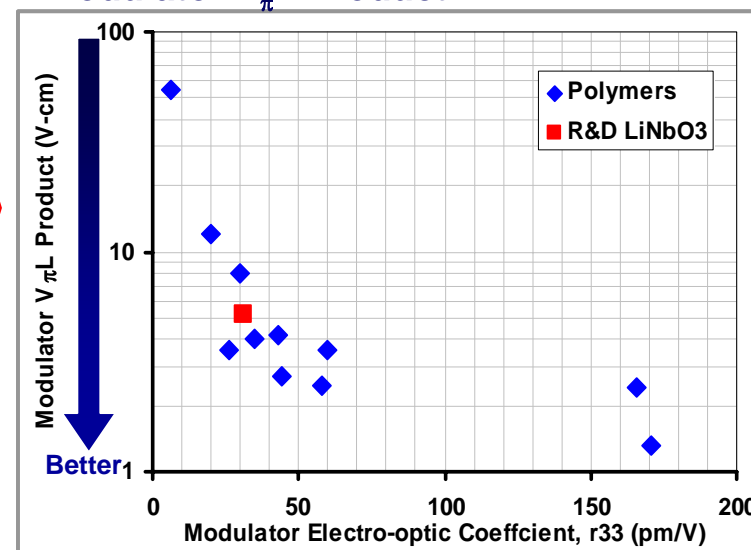
### Material EO Coefficients



Exploit exceptional polymer  $r_{33}$  for better modulator performance

$$V_{\pi} L = \frac{\lambda d}{n^3 r_{33}}$$

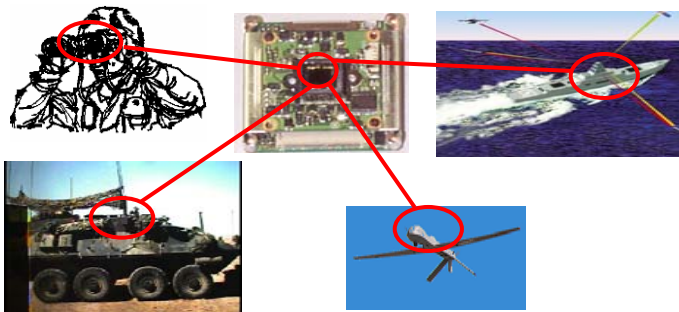
### Modulator $V_{\pi} L$ Product





# Sensor Protection

## $\chi^{(3)}$ Materials and Components



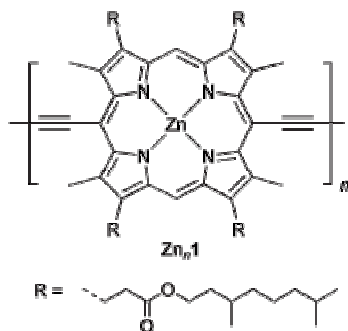
### Program Goals



Transmission @ 700-900 nm	>80%
Transmission @ 1530-1640 nm	>70%
Suppression	30 dB

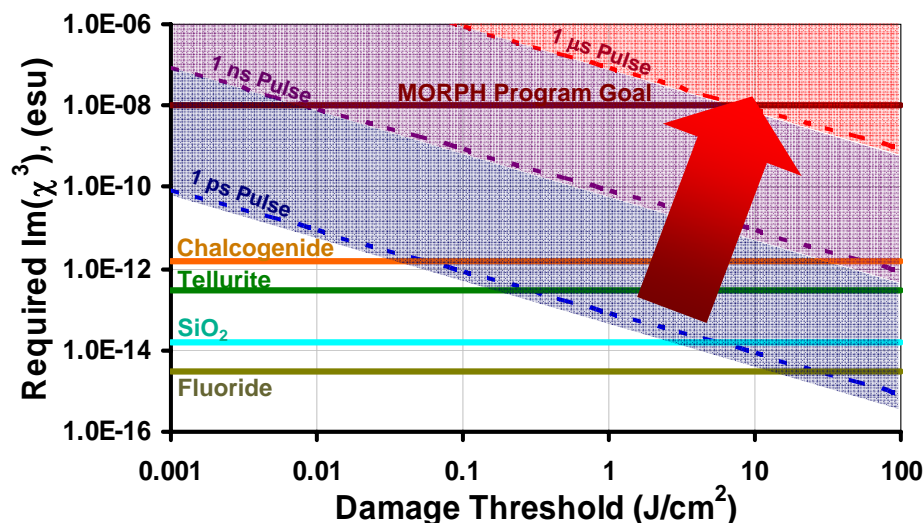
femto→pico→micro-second pulses

Protection from ultra-short pulsed and broadband tunable lasers



HLApol-Zn

$\chi^{(3)}$  versus Sensor Damage Threshold



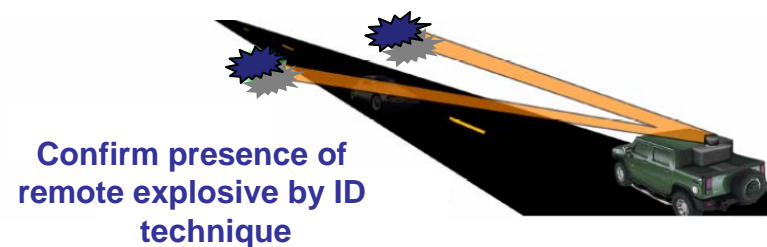
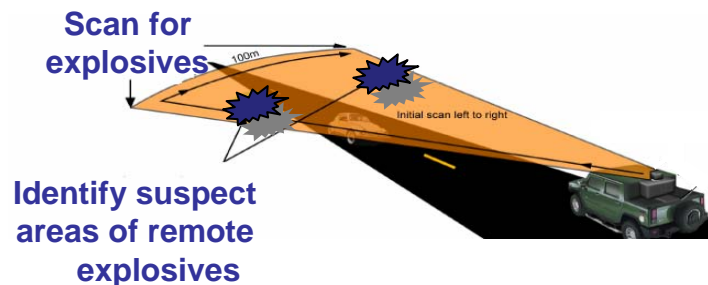
New  $\chi^{(3)}$  Optical Materials will Enable Sensor Protection Systems



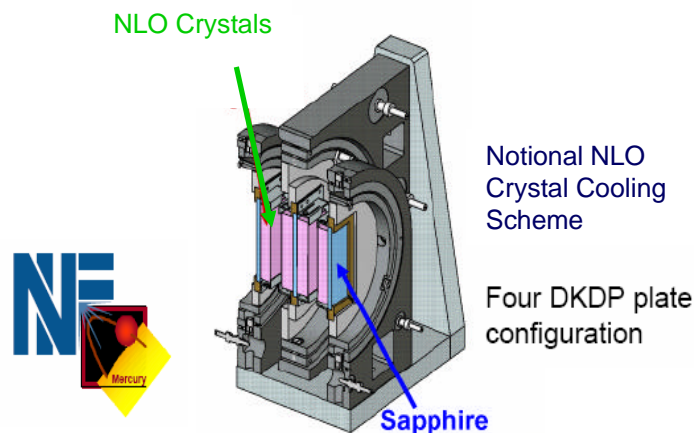


# High-Power Lasers

## *High-efficiency NLO materials*



**Explosives detection at a distance using compact short- wavelength high power lasers and orthogonal optical spectroscopy techniques**



**Exploit compact high-power lasers at long wavelengths and use NLO crystals to convert to desired wavelength**

- Thermal and defect damage resistance
- High-efficiency NLO materials for high-fluence applications



**High-efficiency NLO materials will enable remote explosives detection**

Dr. Devanand Shenoy

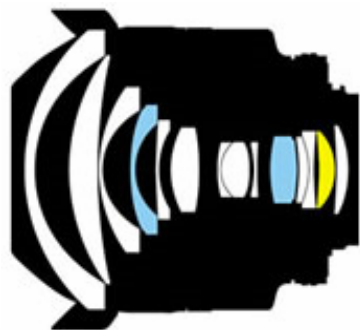
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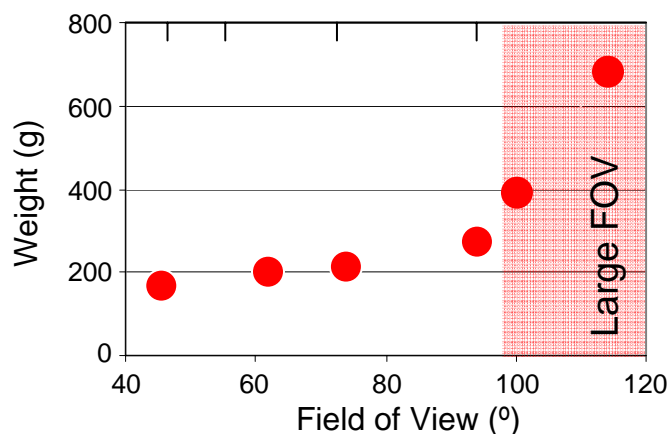


# Compact Camera

## New Materials & Processes

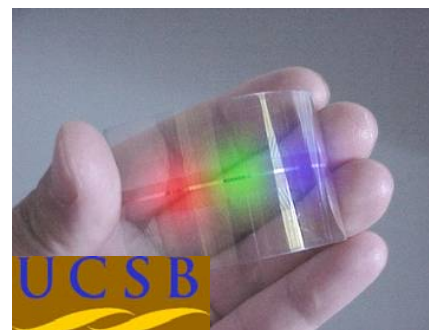
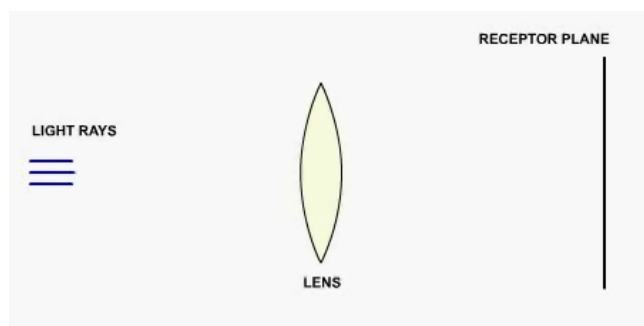


14 lenses, 2 aspherics

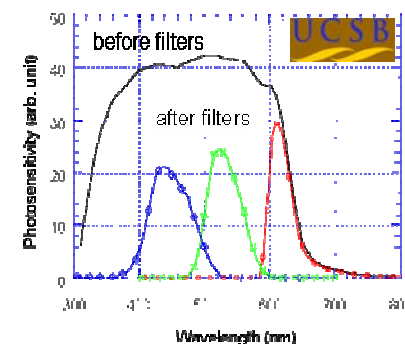


Source: Nikon

*Large field-of-view cameras need multiple lenses to correct for aberrations due to a flat focal plane*



Organic photo-detector in VIS



**Exploit process able photo-diodes to manufacture curved focal planes for the VIS, NIR and SWIR bands**



# Efficient Energy-Harvesting Devices

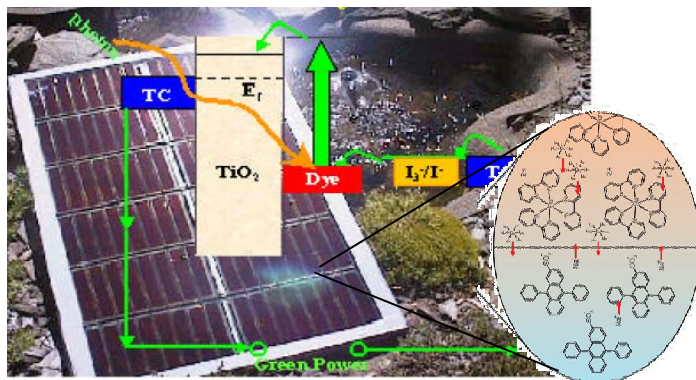
## *Flexible Photovoltaics*



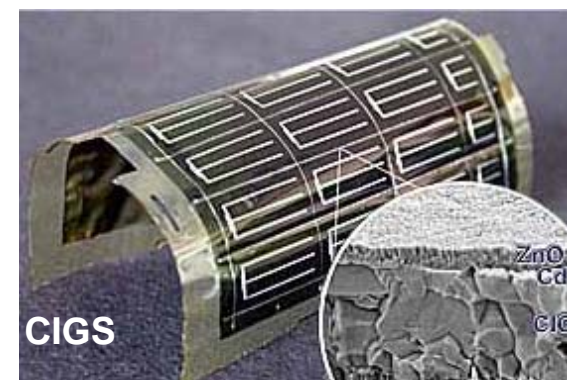
- Low efficiency
- Heavy
- Poor flexibility
- High cost

- New Organic/bioinspired materials

- Thin film inorganics (CIGS)



**3<sup>rd</sup> generation technologies with Increased stability and efficiency**



**Enabling low-cost, versatile photovoltaics for large-scale power generation**

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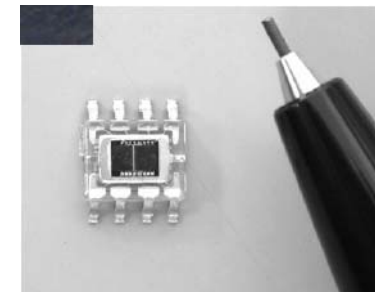
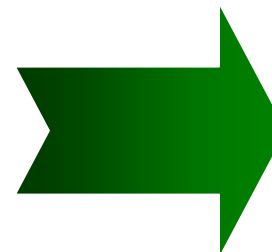
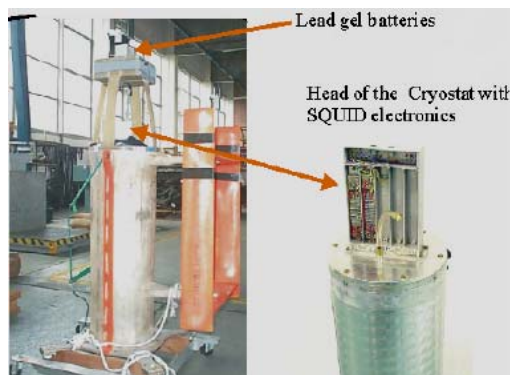


# Magnetic Sensors

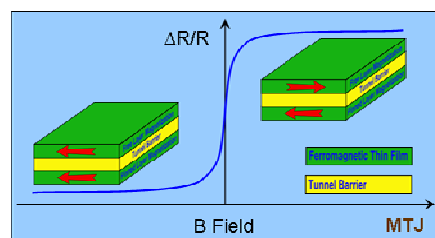
## New Magneto-resistive Materials



**Current high-sensitivity magnetic sensors are bulky**

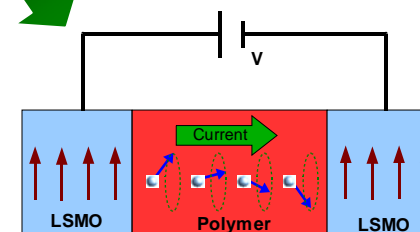


**Novel Materials enable MR in excess of 400%!**



**MTJ Devices**

**Novel polymer-based devices**



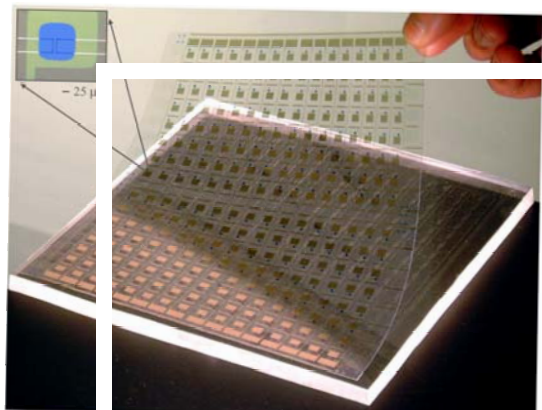
**Spin Injection Based Devices**

**Miniature room-temperature, low-frequency magnetic sensors**

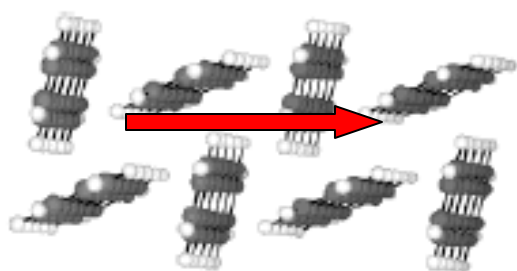


# Organic TFTs

## Organic Semiconductors

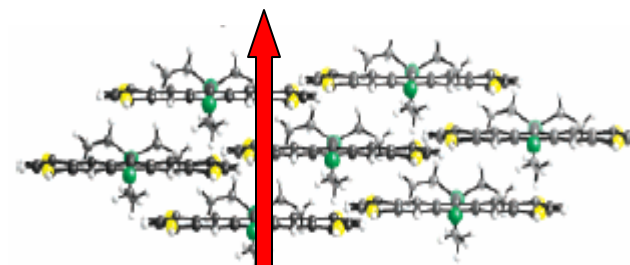


*Organic transistors are process able at low-cost but have poor performance*



Crystal engineering

$$\mu \propto t_{ij}^2 \sqrt{\frac{\pi}{\hbar k_B T \lambda}} e^{-\frac{(\Delta E - \lambda)^2}{4 \lambda k_B T}}$$



*Control of the relative arrangement of the molecules in a solid coupled to theoretical semiconductor performance*

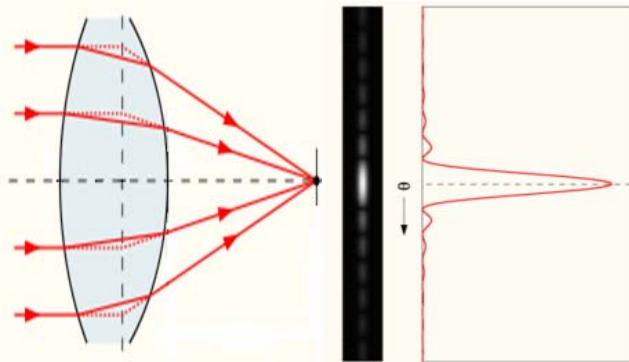
**Ordered organic semiconductors for higher-end performance and flexible distributed electronics**



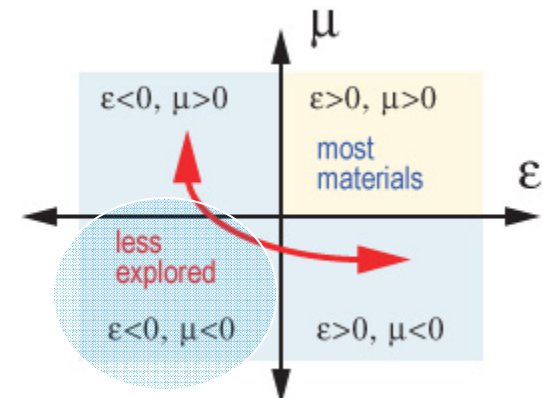


# Superlens

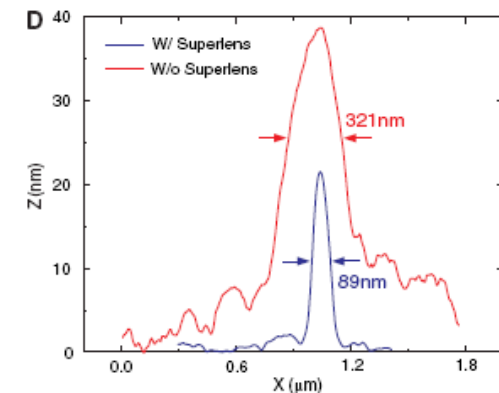
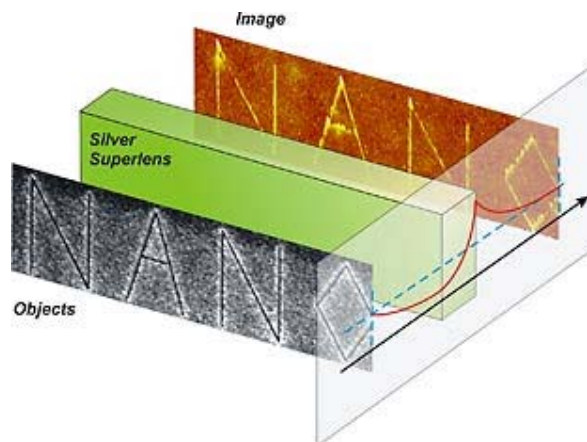
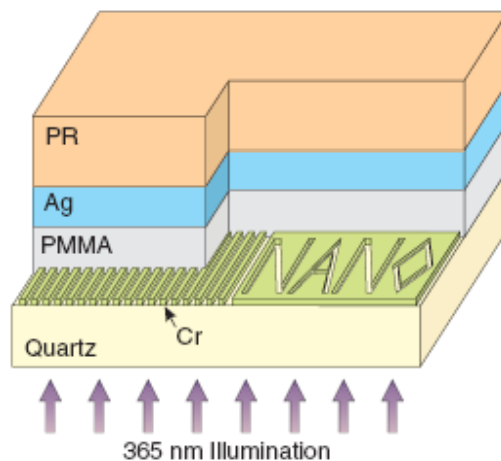
## Negative Index Materials



Diffraction limits the performance of current optical elements



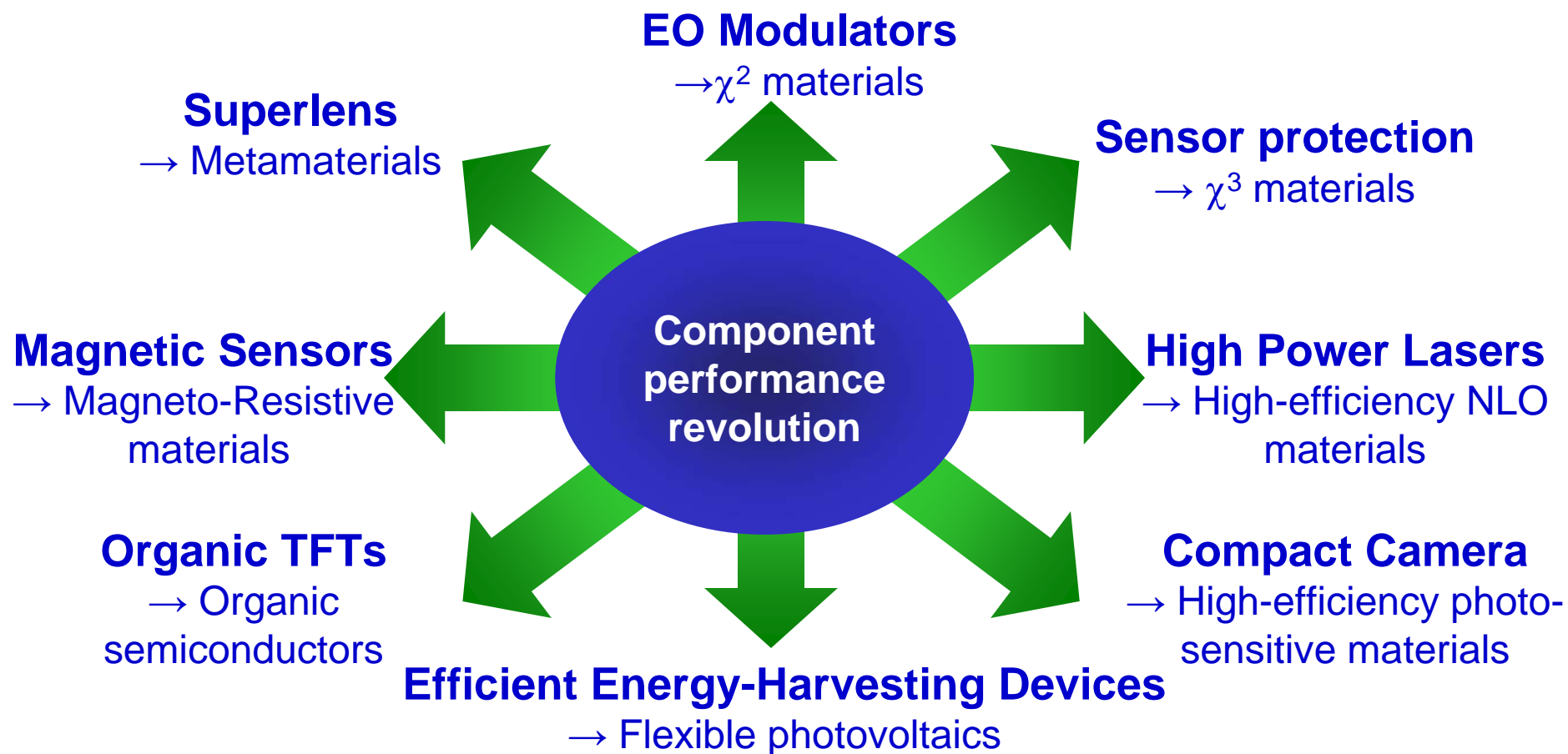
Metamaterials for sub-diffraction limited imaging



Sub-diffraction optical imaging



# Components and Devices for New Military Capabilities



**Leverage High-Performance Materials for Revolutionary Photonic, Electronic, & Magnetic Components**

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